

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 30A, V_{CE} = 10V$, Note 1	11	19	S
C_{ies} C_{oes} C_{res}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		1750	pF
			120	pF
			46	pF
Q_g Q_{ge} Q_{gc}	$I_C = 30A, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		87	nC
			15	nC
			39	nC
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 25^\circ C$ $I_C = 30A, V_{GE} = 15V$, Notes 2 $V_{CE} = 0.8 \cdot V_{CES}, R_G = 5\Omega$		16	ns
			37	ns
			3.47	mJ
			127	ns
			204	ns
			2.16	mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 125^\circ C$ $I_C = 30A, V_{GE} = 15V$, Notes 2 $V_{CE} = 0.8 \cdot V_{CES}, R_G = 5\Omega$		18	ns
			38	ns
			6.70	mJ
			216	ns
			255	ns
			5.10	mJ
R_{thJC} R_{thCS}			0.21	$0.42^\circ C/W$ $^\circ C/W$

Reverse Diode (FRED)

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 30A, V_{GE} = 0V$, Note 1 $T_J = 150^\circ C$		1.6	2.8 V
I_{RM} t_{rr}	$I_F = 30A, V_{GE} = 0V, -di_F/dt = 100A/\mu s, T_J = 100^\circ C$ $V_R = 300V, T_J = 100^\circ C$			4 A
			100	ns
R_{thJC}				$0.9^\circ C/W$

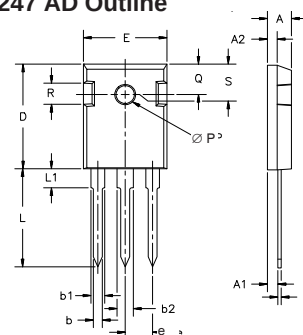
Note 1: Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.

2. Switching times may increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, higher T_J or increased R_G .

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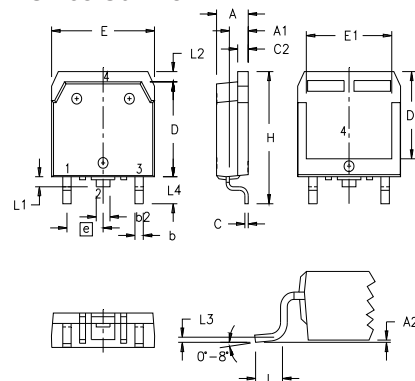
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592 4,850,072 4,881,106	4,931,844 5,017,508 5,034,796	5,049,961 5,063,307 5,187,117	5,237,481 5,381,025 5,486,715	6,162,665 6,259,123 B1 6,306,728 B1	6,404,065 B1 6,534,343 6,583,505	6,683,344 6,710,405 B2 6,710,463	6,727,585 6,759,692 6,771,478 B2	7,005,734 B2 7,063,975 B2 7,071,537	7,157,338 B2
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TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
Q	3.55	3.65	.140	.144
R	5.89	6.40	0.232	0.252
S	4.32	5.49	.170	.216

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Fig. 1. Output Characteristics
@ 25°C

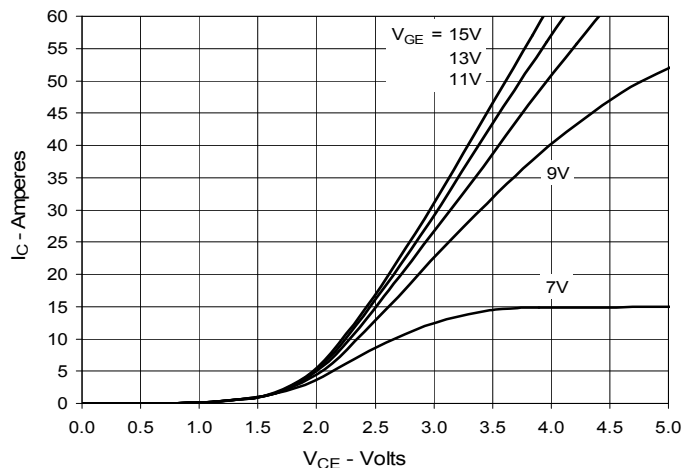


Fig. 2. Extended Output Characteristics
@ 25°C

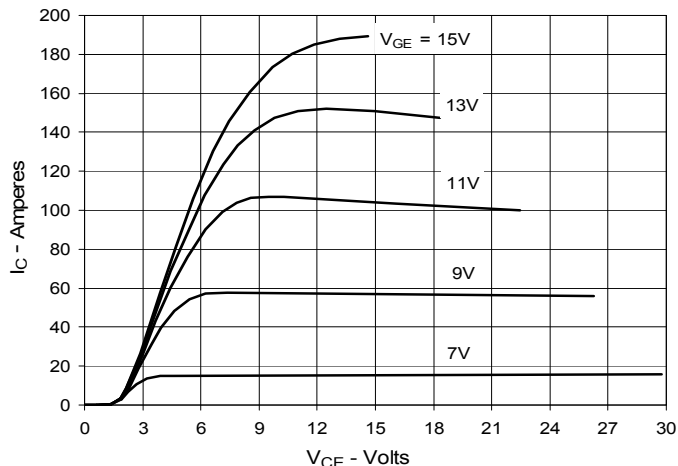


Fig. 3. Output Characteristics
@ 125°C

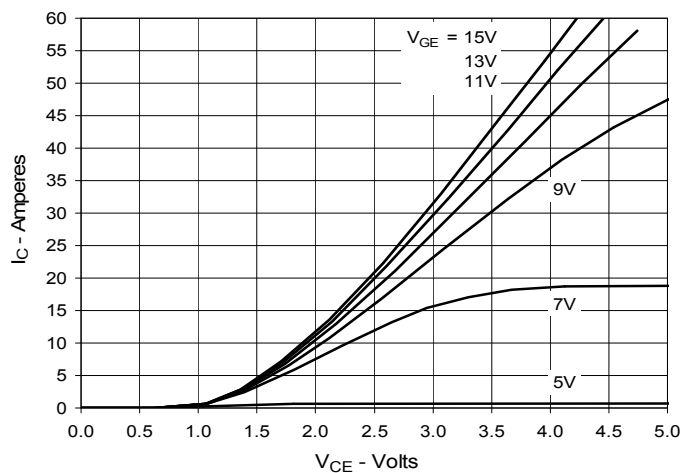


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

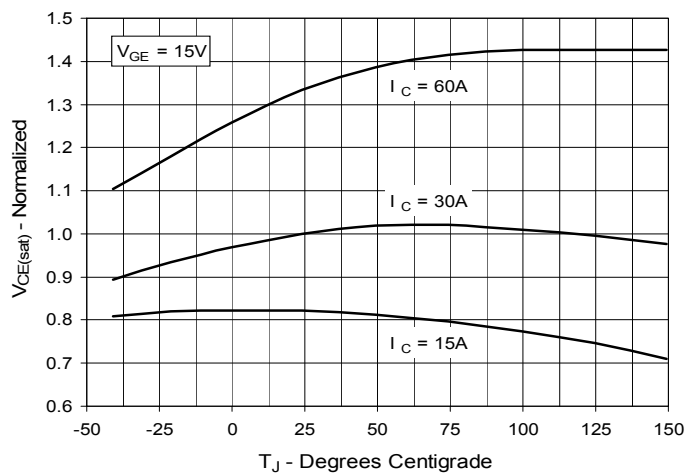


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

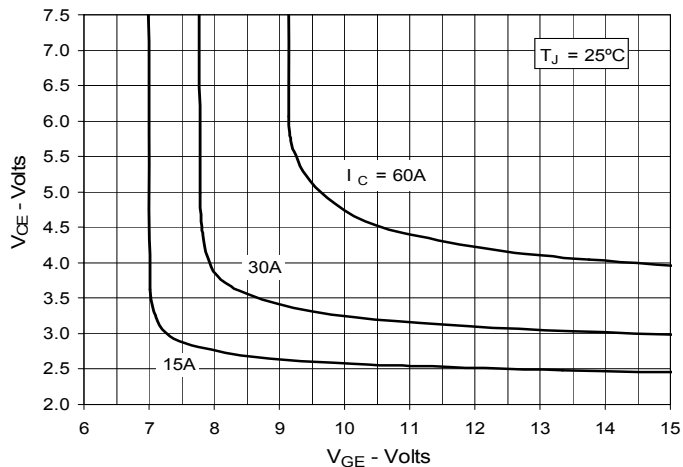


Fig. 6. Input Admittance

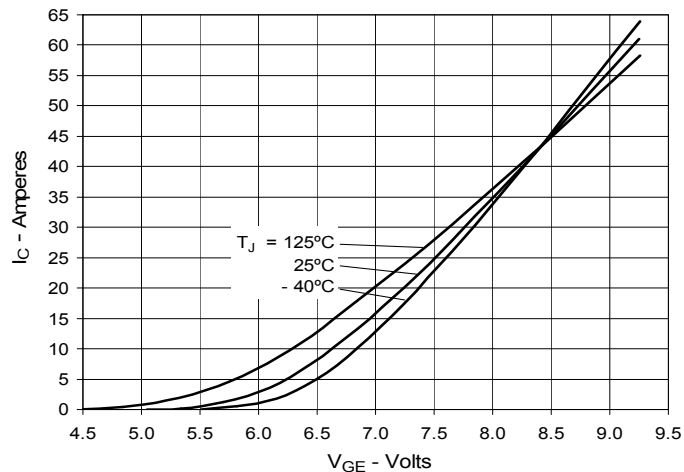


Fig. 7. Transconductance

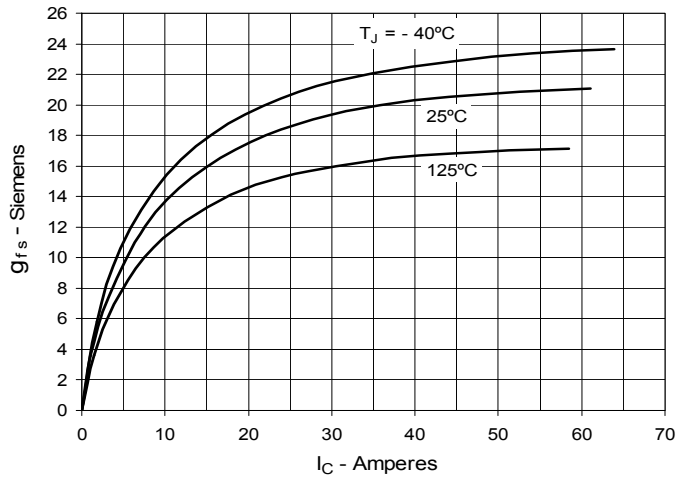


Fig. 8. Gate Charge

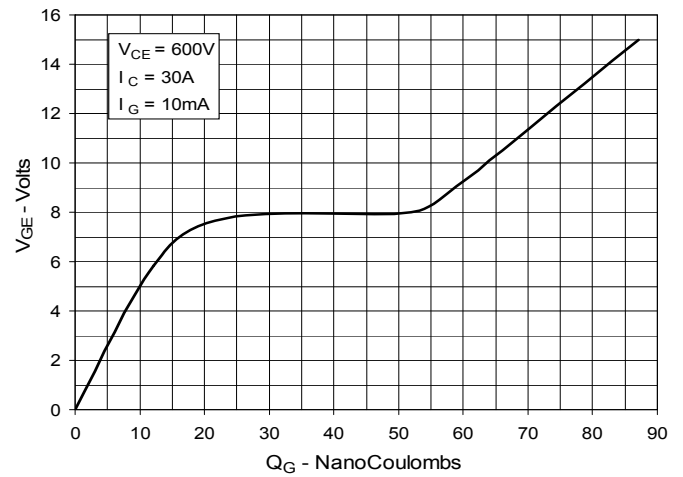


Fig. 9. Capacitance

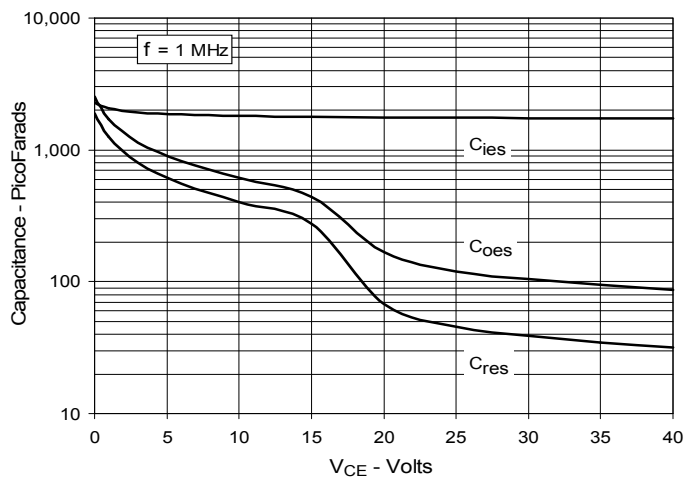


Fig. 10. Reverse-Bias Safe Operating Area

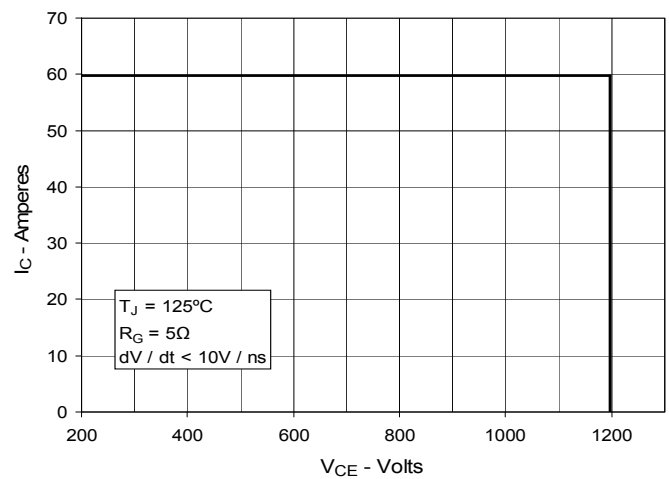
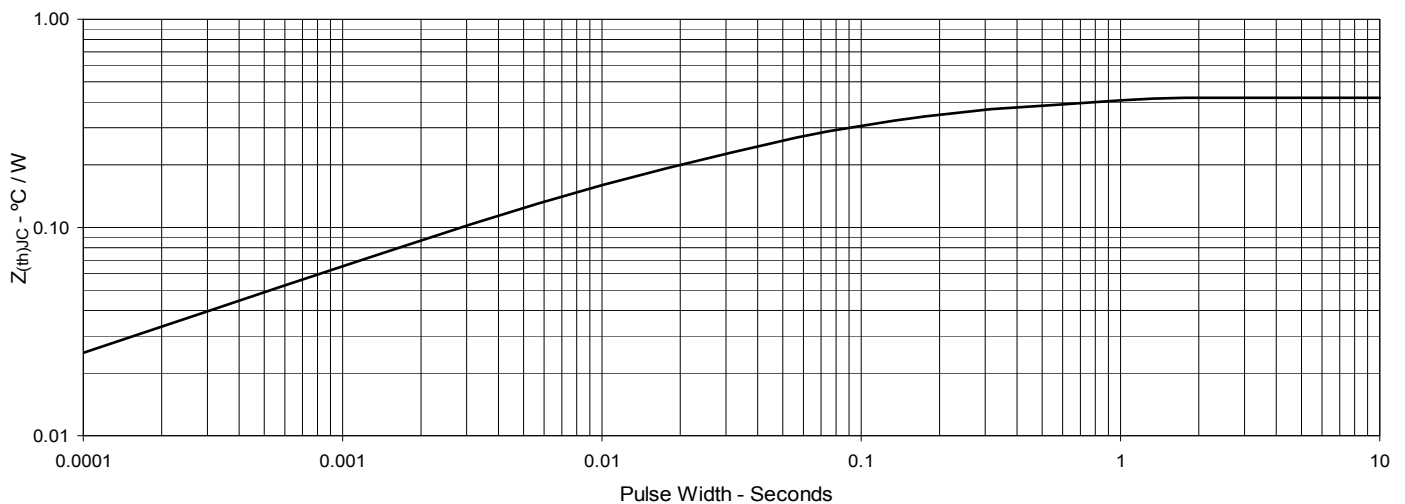
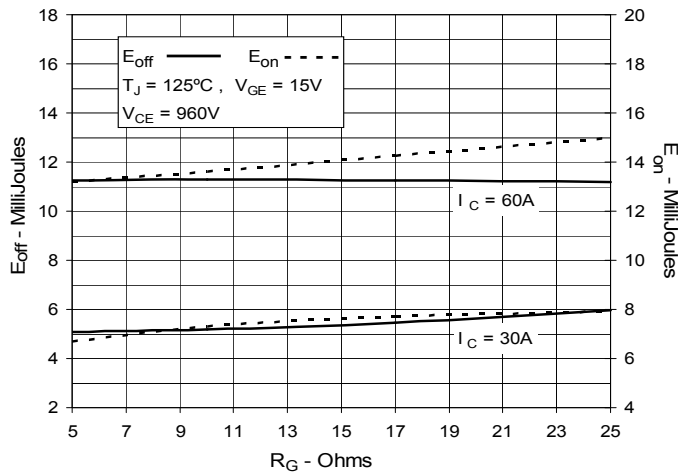


Fig. 11. Maximum Transient Thermal Impedance

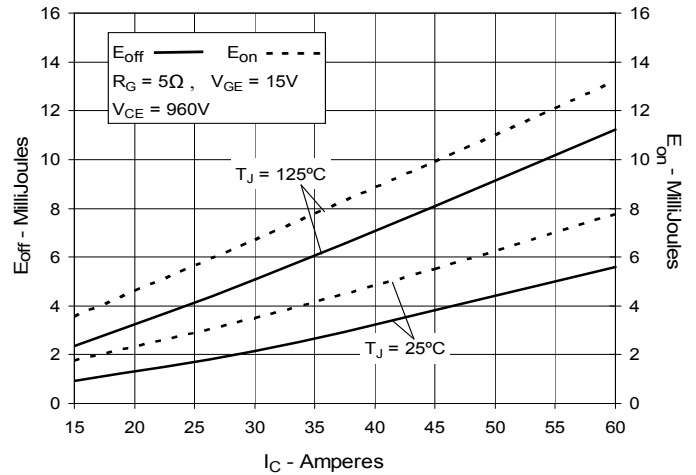


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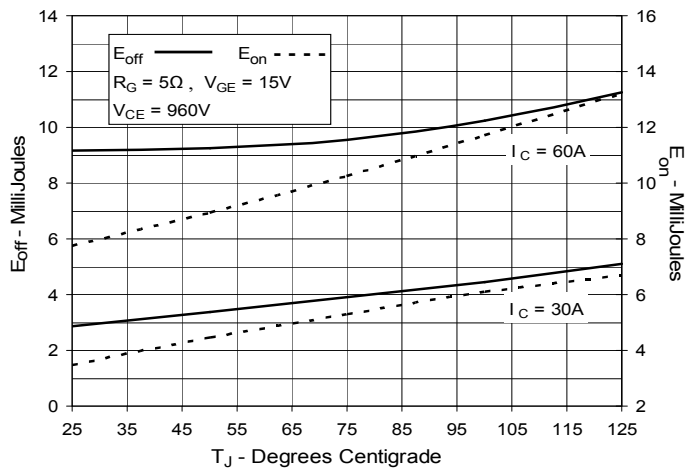
**Fig. 12. Inductive Switching
Energy Loss vs. Gate Resistance**



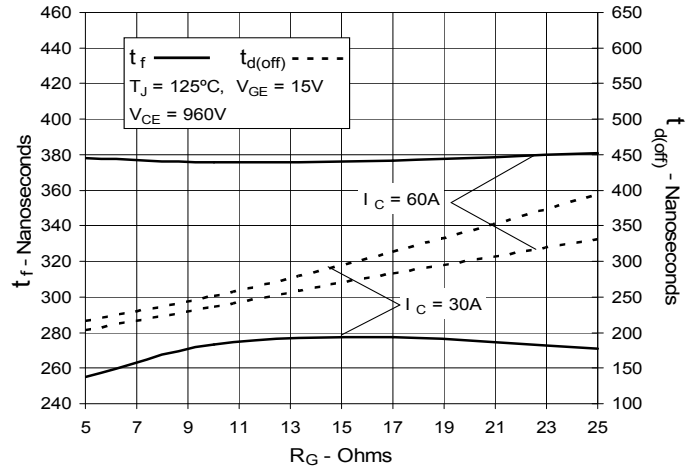
**Fig. 13. Inductive Switching
Energy Loss vs. Collector Current**



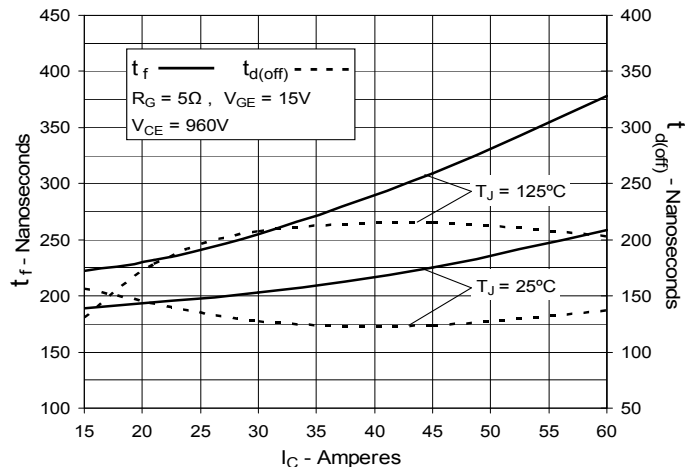
**Fig. 14. Inductive Switching
Energy Loss vs. Junction Temperature**



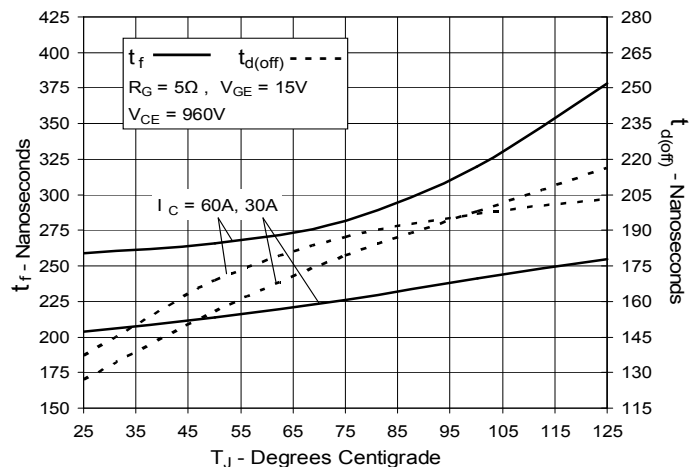
**Fig. 15. Inductive Turn-off
Switching Times vs. Gate Resistance**



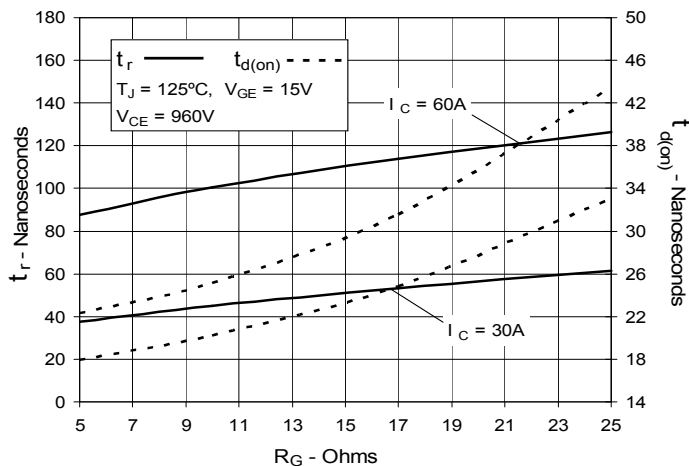
**Fig. 16. Inductive Turn-off
Switching Times vs. Collector Current**



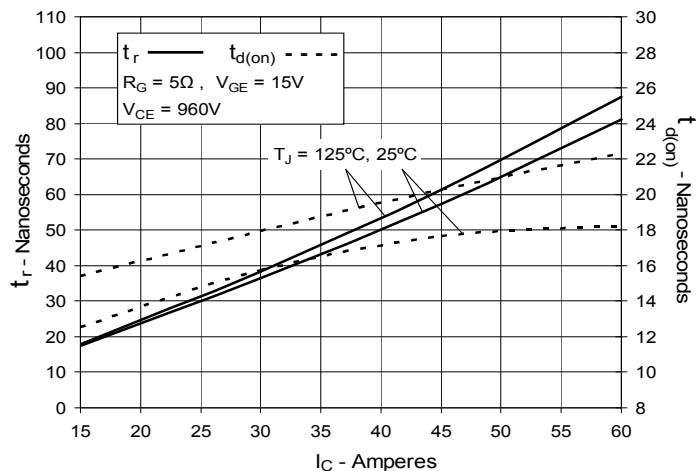
**Fig. 17. Inductive Turn-off
Switching Times vs. Junction Temperature**



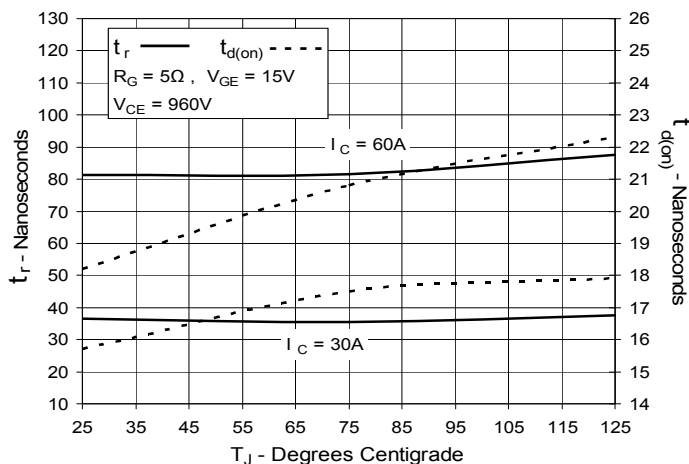
**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**



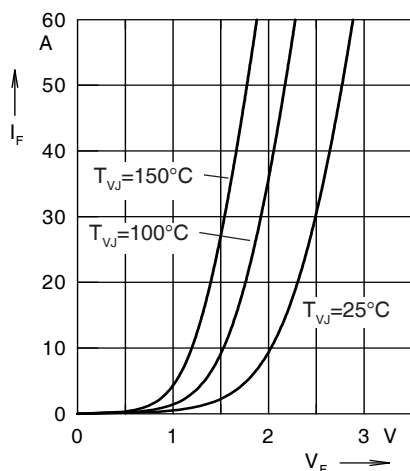


Fig. 21. Forward current I_F versus V_F

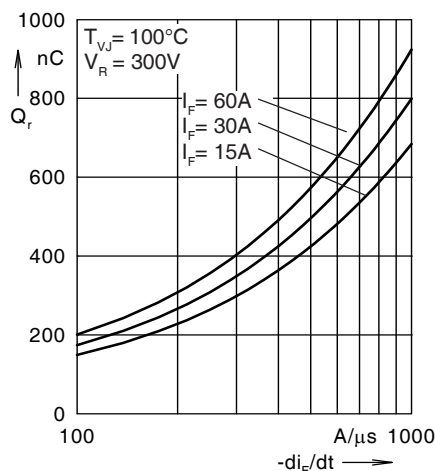


Fig. 22. Reverse recovery charge Q_r versus $-di_F/dt$

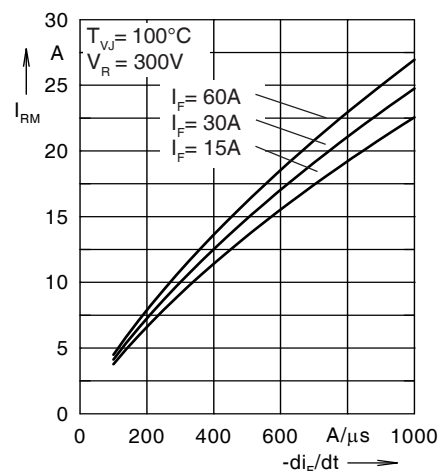


Fig. 23. Peak reverse current I_{RM} versus $-di_F/dt$

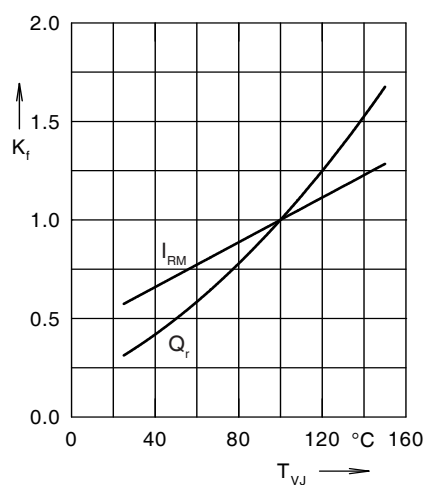


Fig. 24. Dynamic parameters Q_r , I_{RM} versus T_{VJ}

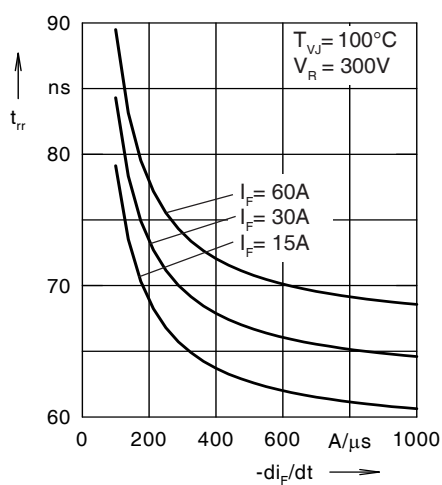


Fig. 25. Recovery time t_{rr} versus $-di_F/dt$

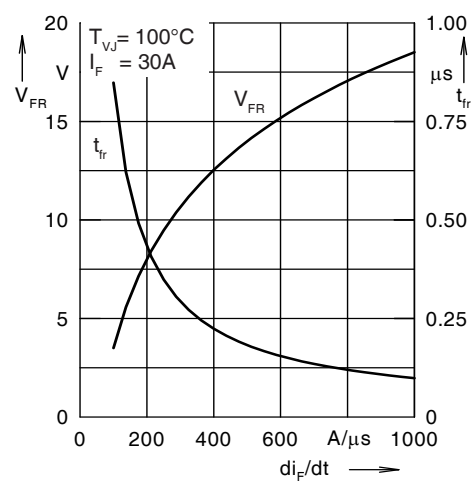


Fig. 26. Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

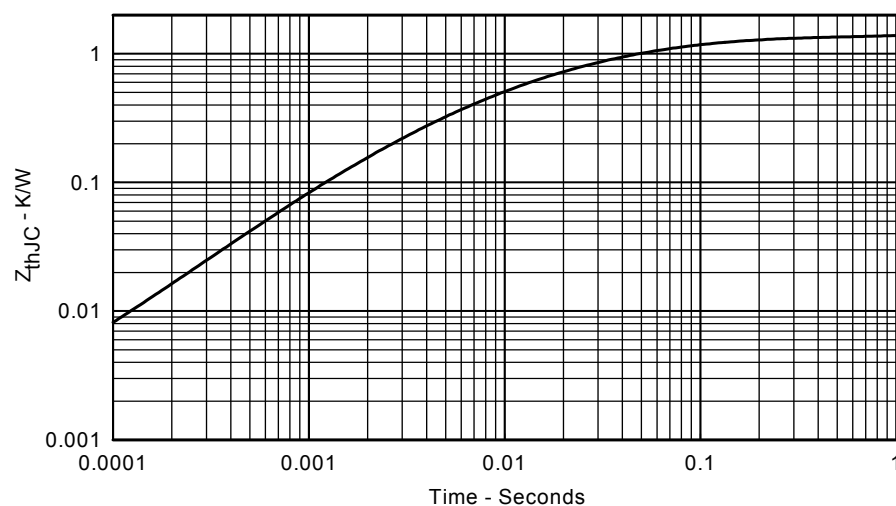


Fig. 27. Transient thermal resistance junction to case



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